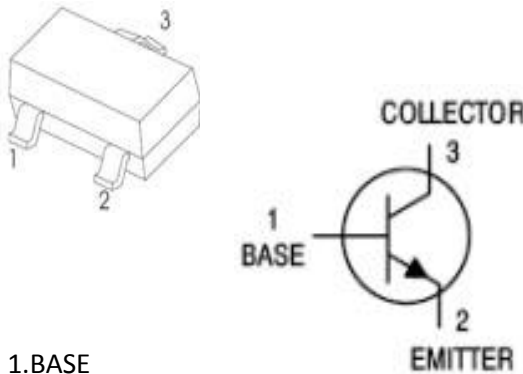


TRANSI STOR (NPN)		SOT-23 Plastic-Encapsulate Transistors																																					
<u>SOT-23</u>  1.BASE 2.EMITTER 3.COLLECTOR		Features ※ Complimentary to 2SA812 ※ Collector Current: Ic=0.1A																																					
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted) <table><tr><th>Parameter</th><th>Symbol</th><th>Value</th><th>Unit</th></tr><tr><td>Collector-Base Voltage</td><td>VCBO</td><td>60</td><td>V</td></tr><tr><td>Collector-Emitter Voltage</td><td>VCEO</td><td>50</td><td>V</td></tr><tr><td>Emitter-Base Voltage</td><td>VEBO</td><td>6</td><td>V</td></tr><tr><td>Collector Current</td><td>IC</td><td>100</td><td>mA</td></tr><tr><td>Collector Power Dissipation</td><td>PC</td><td>450</td><td>mW</td></tr><tr><td>Thermal Resistance From Junction To Ambient</td><td>RθJA</td><td>625</td><td>℃/W</td></tr><tr><td>Junction Temperature</td><td>Tj</td><td>150</td><td>℃</td></tr><tr><td>Storage Temperature</td><td>Tstg</td><td>-55~+150</td><td>℃</td></tr></table>				Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	60	V	Collector-Emitter Voltage	VCEO	50	V	Emitter-Base Voltage	VEBO	6	V	Collector Current	IC	100	mA	Collector Power Dissipation	PC	450	mW	Thermal Resistance From Junction To Ambient	RθJA	625	℃/W	Junction Temperature	Tj	150	℃	Storage Temperature	Tstg	-55~+150	℃
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ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	60	126	200	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	50	55	100	V
Emitter-base breakdown voltage	V(BR)EBO	IE= 100μA, IC=0	6	7.5	30	V
Collector cut-off current	ICBO	VCE= 60 V , IE=0			0.1	μA
Collector cut-off current	ICEO	VCE= 50V , IB=0			0.1	μA
Emitter cut-off current	IEBO	VEB= 6V , IC=0			0.1	μA
DC current gain	hFE	VCE=6V, IC= 1mA	200		1000	
	hFE	VCE=6V, IC= 10mA	100			
Collector-emitter saturation voltage	VCE(sat)	IC=100 mA, IB= 10mA			0.3	V
Base-emitter saturation voltage	VBE(sat)	IC=100 mA, IB= 10mA			1.3	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	150			MHz

LASSIFICATION OF hFE

Rank	L4	L5	L6	L7
Range	90-180	135-270	200-400	400-600
MARKING	L4	L5	L6	L7

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

